MJD44E3, NJVMJD44E3T4G

Darlington Power Transistor

DPAK For Surface Mount Applications

Designed for general purpose power and switching output or driver stages in applications such as switching regulators, converters, and power amplifiers.

Features

- Electrically Similar to Popular D44E3 Device
- High DC Gain 1000 Min @ 5.0 Adc
- Low Sat. Voltage 1.5 V @ 5.0 Adc
- Compatible With Existing Automatic Pick and Place Equipment
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings:
 - Human Body Model, 3B > 8000 V
 - Machine Model, C > 400 V
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb–Free Packages*

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Emitter-Base Voltage	V _{EB}	7	Vdc
Collector Current - Continuous	Ic	10	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	20 0.16	W W/°C
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1



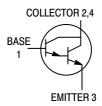
ON Semiconductor®

http://onsemi.com

NPN DARLINGTON SILICON POWER TRANSISTORS 10 AMPERES 80 VOLTS, 20 WATTS



DPAK CASE 369C STYLE 1



MARKING DIAGRAM



A = Assembly Location

Y = Year
WW = Work Week
J44E3 = Device Code
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MJD44E3T4G	DPAK (Pb-Free)	2,500 / Tape & Reel
NJVMJD44E3T4G	DPAK (Pb-Free)	2,500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

These ratings are applicable when surface mounted on the minimum pad sizes recommended.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MJD44E3, NJVMJD44E3T4G

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ hetaJC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	71.4	°C/W
Lead Temperature for Soldering	TL	260	°C

^{2.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

_					
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector Cutoff Current $(V_{CE} = Rated V_{CEO}, V_{BE} = 0)$	I _{CES}	-	_	10	μΑ
Emitter Cutoff Current (V _{EB} = 7 Vdc)	I _{EBO}	-	_	1	μΑ
ON CHARACTERISTICS					
Collector–Emitter Saturation Voltage ($I_C = 5$ Adc, $I_B = 10$ mAdc) ($I_C = 10$ Adc, $I_B = 20$ mAdc)	V _{CE(sat)}	- -	- -	1.5 2	Vdc
Base-Emitter Saturation Voltage (I _C = 5 Adc, I _B = 10 mAdc)	V _{BE(sat)}	-	-	2.5	Vdc
DC Current Gain (V _{CE} = 5 Vdc, I _C = 5 Adc)	h _{FE}	1000	-	-	_
DYNAMIC CHARACTERISTICS					
Collector Capacitance (V _{CB} = 10 Vdc, f _{test} = 1 MHz)	C _{cb}	-	-	130	pF
SWITCHING TIMES					
Delay and Rise Times (I _C = 10 Adc, I _{B1} = 20 mAdc)	t _d + t _r	-	0.6	-	μs
Storage Time (I _C = 10 Adc, I _{B1} = I _{B2} = 20 mAdc)	t _s	-	2	-	μs
Fall Time (I _C = 10 Adc, I _{B1} = I _{B2} = 20 mAdc)	t _f	-	0.5	-	μs

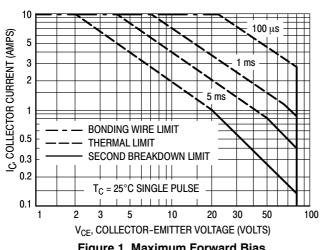


Figure 1. Maximum Forward Bias Safe Operating Area

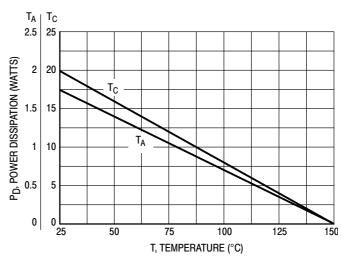
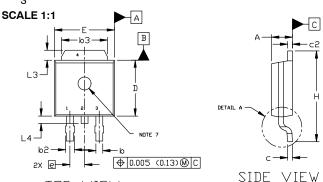


Figure 2. Power Derating



DPAK (SINGLE GAUGE) CASE 369C **ISSUE G**

DATE 31 MAY 2023





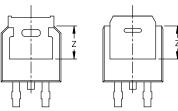
- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS 63,
- L3. AND Z. L3, AND Z.

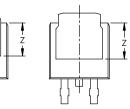
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR
 GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
 DIMENSIONS D AND E ARE DETERMINED AT THE
 OUTERMOST EXTREMES OF THE PLASTIC BODY.
 DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
 DETININAL MOLD ESCALUPE.

- OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b 3	0.180	0.215	4.57	5.46
Ū	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
Η	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020 BSC		0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040	-	1.01
Z	0.155		3.93	

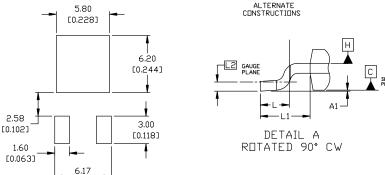
TOP VIEW



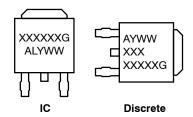


BOTTOM VIEW

BOTTOM VIEW



GENERIC MARKING DIAGRAM*



XXXXXX	= Device Code
Α	= Assembly Location
L	= Wafer Lot
Υ	= Year
WW	= Work Week
G	= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT* *FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DUWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

[0.243]

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. COLLECTOR	2. DRAIN	2. CATHODE	2. ANODE	2. ANODE
EMITTER	3. SOURCE	3. ANODE	3. GATE	CATHODE
COLLECTOR	4. DRAIN	CATHODE	4. ANODE	ANODE

4. COLLEC		4. DRAIN	ANODE ANODE ANODE	3. GATE 4. ANODE	3. CATHODE 4. ANODE
TYLE 6: S	STYLE 7: PIN 1. GATE	,		E 9: 1. ANODE	STYLE 10: PIN 1. CATHODE

2. MT2 3. GATE 4. MT2 2. CATHODE 3. RESISTOR ADJUST 2. ANODE 3. CATHODE 3 ANODE 3 FMITTER 4. COLLECTOR 4. CATHODE 4. CATHODE 4. ANODE

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1	

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